

## Silicon PIN Photodiode



21726

### DESCRIPTION

VBPW34FAS and VBPW34FASR are high speed and high sensitive PIN photodiodes. It is a surface mount device (SMD) including the chip with a 7.5 mm<sup>2</sup> sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength 870 nm or 950 nm.

### FEATURES

- Package type: surface mount
- Package form: GW, RGW
- Dimensions (L x W x H in mm): 6.4 x 3.9 x 1.2
- Radiant sensitive area (in mm<sup>2</sup>): 7.5
- High radiant sensitivity
- Daylight blocking filter matched with 870 nm to 950 nm emitters
- Fast response times
- Angle of half sensitivity:  $\varphi = \pm 65^\circ$
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmissionsystems, e.g. in combination with TSFFxxxx series IR emitters

### PRODUCT SUMMARY

COMPONENT	$I_{ra}$ ( $\mu A$ )	$\varphi$ (deg)	$\lambda_{0.5}$ (nm)
VBPW34FAS	55	$\pm 65$	780 to 1050
VBPW34FASR	55	$\pm 65$	780 to 1050

#### Note

- Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VBPW34FAS	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing
VBPW34FASR	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ C$ , unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	60	V
Power dissipation	$T_{amb} \leq 25^\circ C$	$P_V$	215	mW
Junction temperature		$T_j$	100	$^\circ C$
Operating temperature range		$T_{amb}$	- 40 to + 100	$^\circ C$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ C$
Soldering temperature	Acc. reflow solder profile fig. 8	$T_{sd}$	260	$^\circ C$
Thermal resistance junction/ambient		$R_{thJA}$	350	K/W

<b>BASIC CHARACTERISTICS</b> ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50\text{ mA}$	$V_F$		1	1.3	V
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$ , $E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10\text{ V}$ , $E = 0$	$I_{ro}$		2	30	nA
Diode capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_D$		70		pF
	$V_R = 3\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_D$		25	40	pF
Open circuit voltage	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$V_o$		350		mV
Temperature coefficient of $V_o$	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$TK_{V_o}$		-2.6		mV/K
Short circuit current	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$I_k$		50		$\mu\text{A}$
Temperature coefficient of $I_k$	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$TK_{I_k}$		0.1		%/K
Reverse light current	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$ , $V_R = 5\text{ V}$	$I_{ra}$	45	55		$\mu\text{A}$
Angle of half sensitivity		$\varphi$		$\pm 65$		deg
Wavelength of peak sensitivity		$\lambda_p$		950		nm
Range of spectral bandwidth		$\lambda_{0.5}$		780 to 1050		nm
Noise equivalent power	$V_R = 10\text{ V}$ , $\lambda = 950\text{ nm}$	NEP		$4 \times 10^{-14}$		$\text{W}/\sqrt{\text{Hz}}$
Rise time	$V_R = 10\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 820\text{ nm}$	$t_r$		100		ns
Fall time	$V_R = 10\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 820\text{ nm}$	$t_f$		100		ns

## BASIC CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

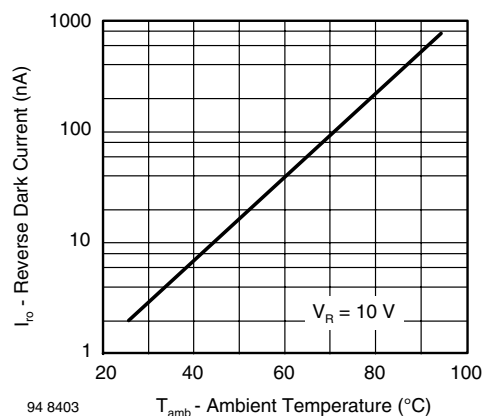


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

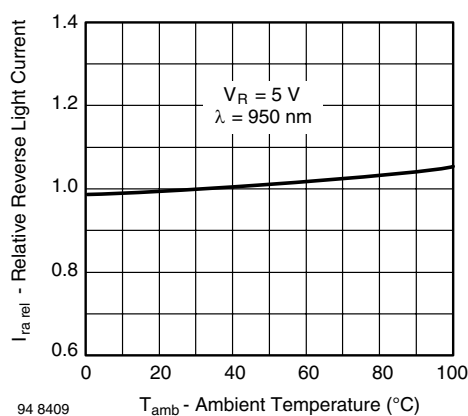
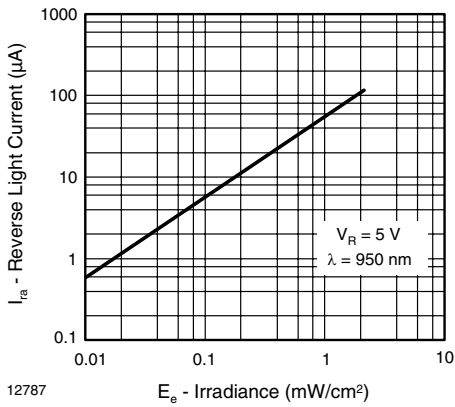
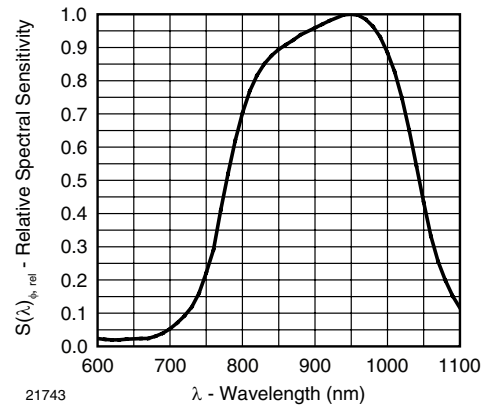


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



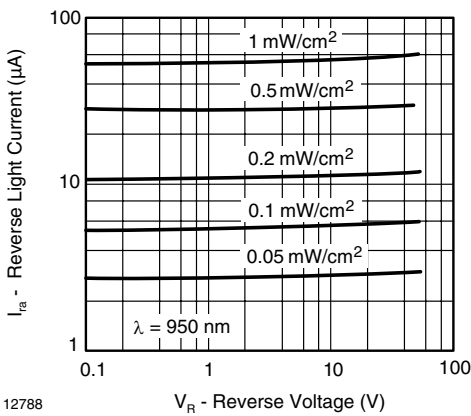
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Fig. 3 - Reverse Light Current vs. Irradiance



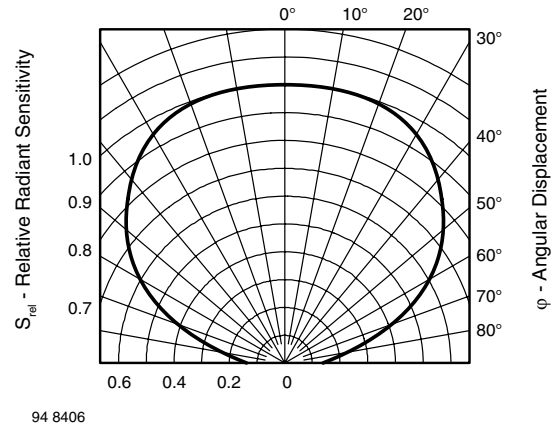
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Fig. 6 - Relative Spectral Sensitivity vs. Wavelength



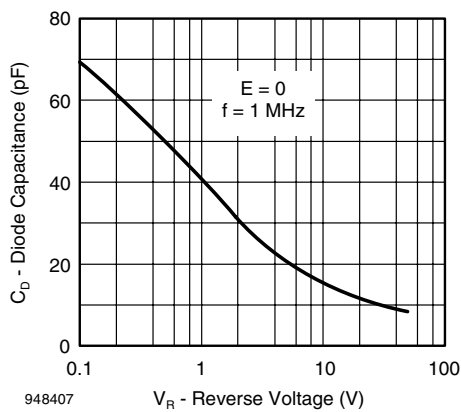
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Fig. 4 - Reverse Light Current vs. Reverse Voltage



94 8406

Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement



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Fig. 5 - Diode Capacitance vs. Reverse Voltage

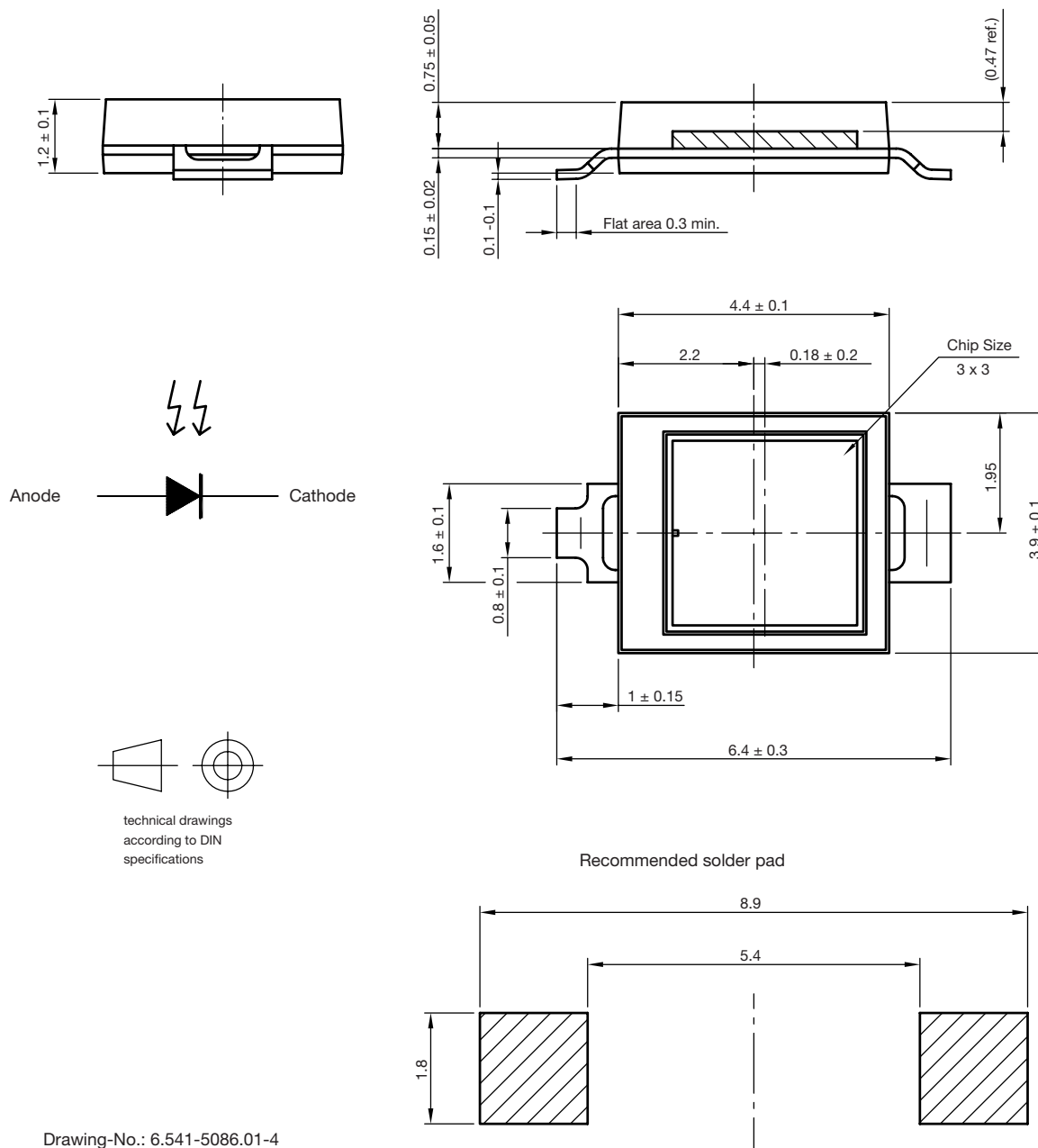
# VBPW34FAS, VBPW34FASR

Vishay Semiconductors

Silicon PIN Photodiode



## PACKAGE DIMENSIONS FOR VBPW34FAS in millimeters

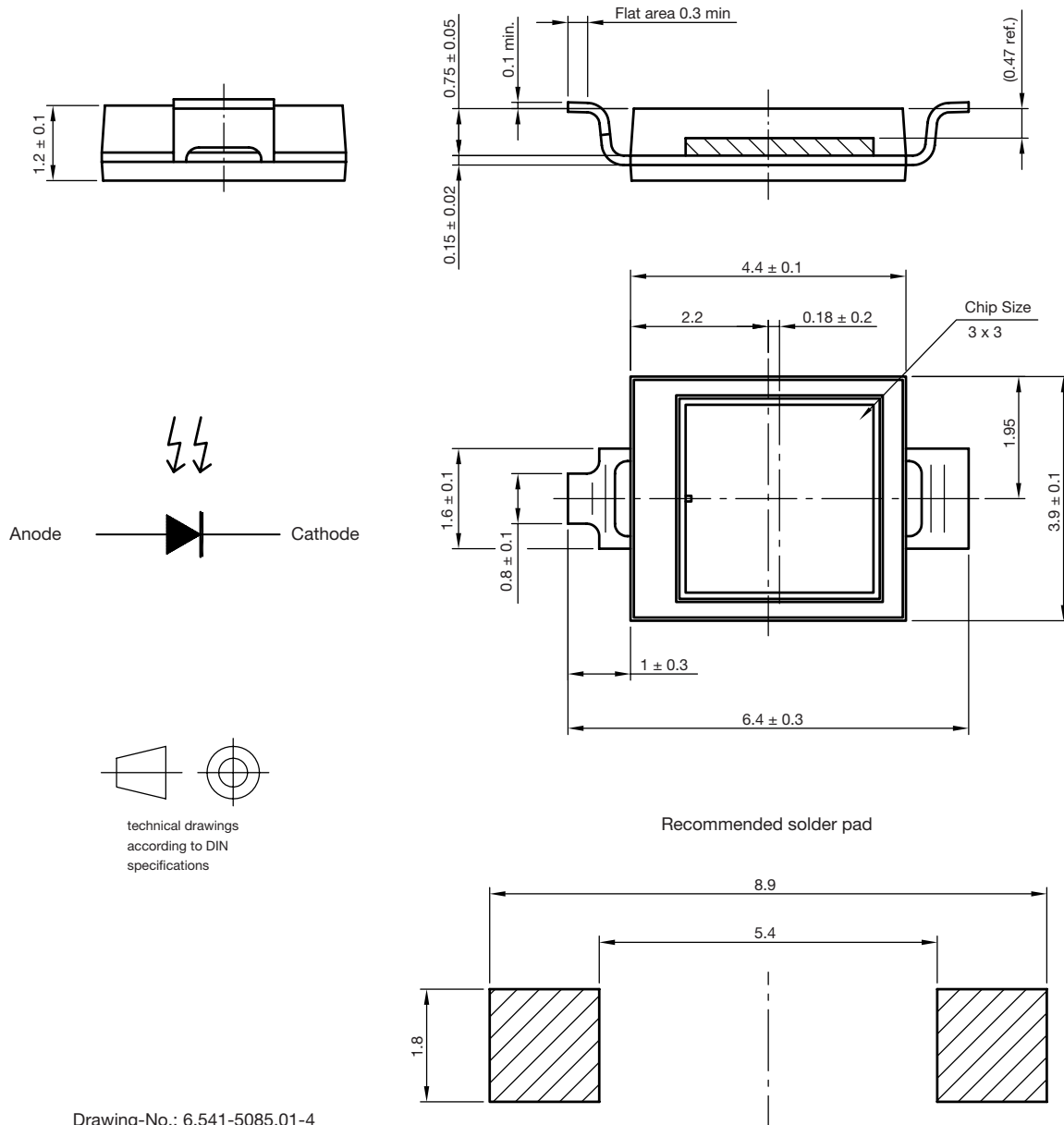


Drawing-No.: 6.541-5086.01-4

Issue: 1; 15.04.10

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## PACKAGE DIMENSIONS FOR VBPW34FASR in millimeters



Drawing-No.: 6.541-5085.01-4

Issue: 1; 15.04.10

22104

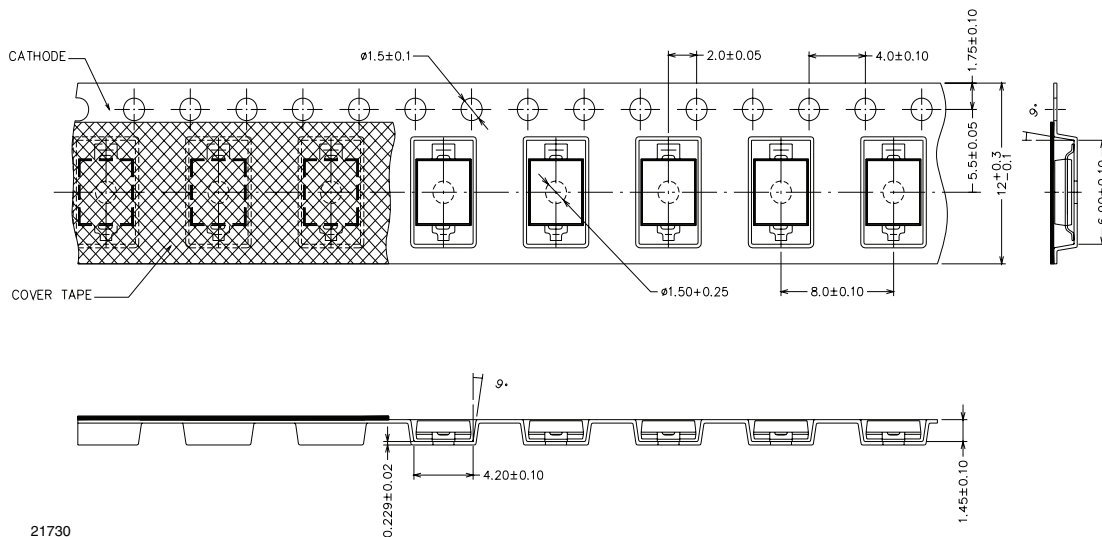
# VBPW34FAS, VBPW34FASR

Vishay Semiconductors

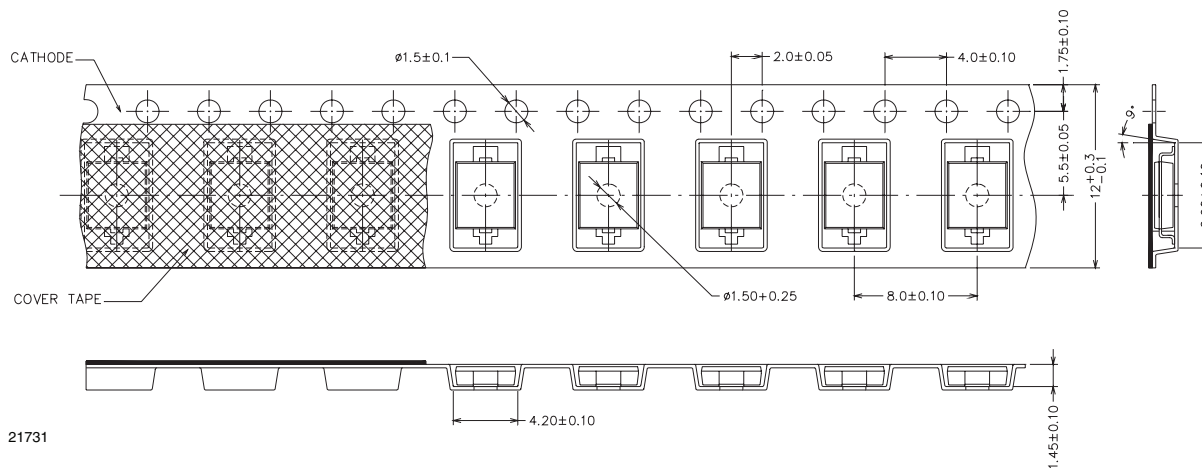
Silicon PIN Photodiode



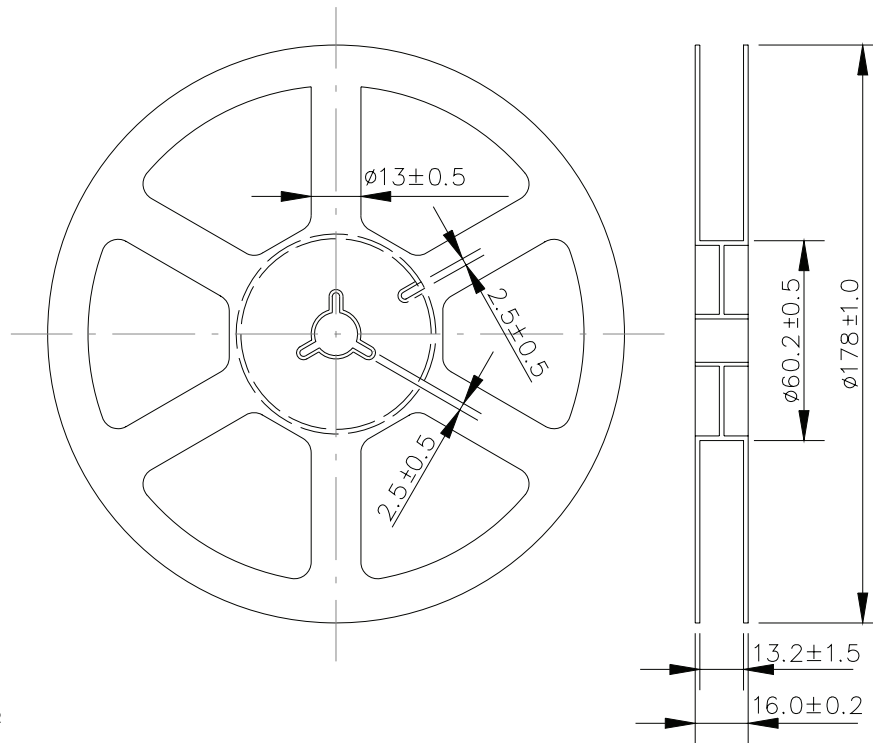
## TAPING DIMENSIONS FOR VBPW34FAS in millimeters



## TAPING DIMENSIONS FOR VBPW34FASR in millimeters

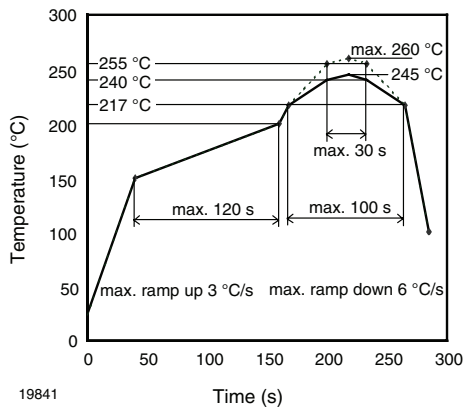


## REEL DIMENSIONS FOR VBPW34FAS AND VBPW34FASR in millimeters



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## SOLDER PROFILE



19841

Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

## DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

## FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 3

Floor life: 168 h

Conditions:  $T_{amb} < 30\text{ }^{\circ}\text{C}$ ,  $\text{RH} < 60\%$

## DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions:

192 h at  $40\text{ }^{\circ}\text{C}$  (+ 5 °C),  $\text{RH} < 5\%$

or

96 h at  $60\text{ }^{\circ}\text{C}$  (+ 5 °C),  $\text{RH} < 5\%$ .



## Disclaimer

All product specifications and data are subject to change without notice.

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